DMC20601

Silicon NPN epitaxial planar type

For general amplification

Features

- High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- Halogen-free / RoHS compliant
- (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

Marking Symbol: B3

Basic Part Number

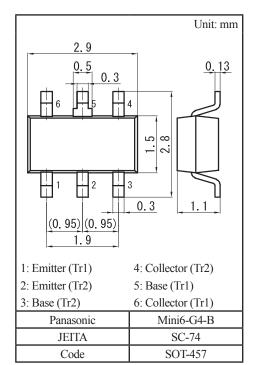
Dual DSC2001 (Individual)

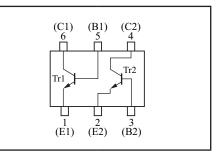
Packaging

DMC206010R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter	Symbol Rating		Unit	
Tr1 Tr2	Collector-base voltage (Emitter open)	V _{CBO}	60	V	
	Collector-emitter voltage (Base open)	V _{CEO}	50	V	
	Emitter-base voltage (Collector open)	V _{EBO}	7	V	
	Collector current	I _C	100	mA	
	Peak collector current	I _{CP}	200	mA	
Overall	Total power dissipation	P _T	300	mW	
	Junction temperature	Tj	150	°C	
	Operating ambient temperature	T _{opr}	T _{opr} -40 to +85		
	Storage temperature	T _{stg}	-55 to +150	°C	

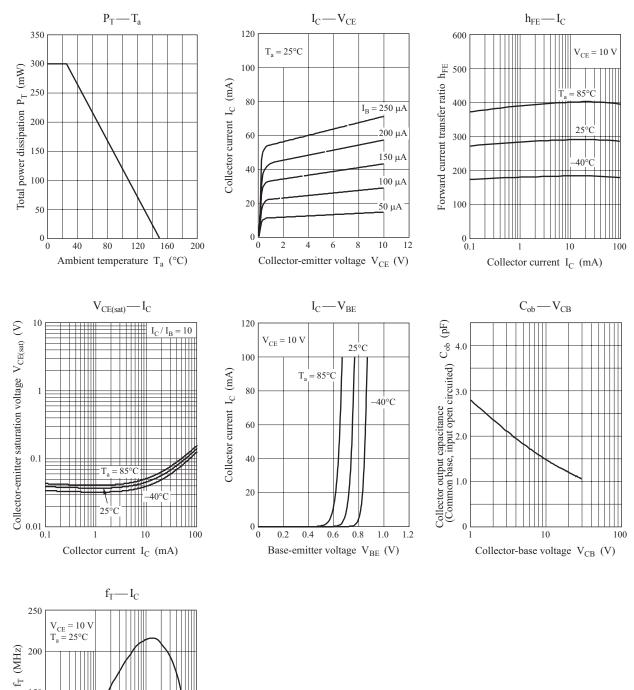


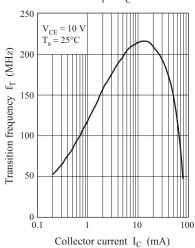


Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

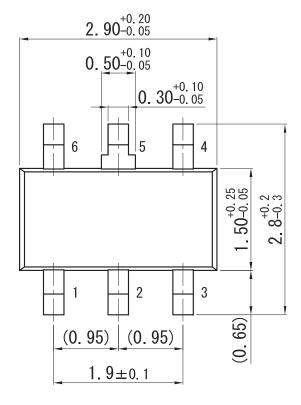
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu {\rm A}, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_B = 0$			100	μΑ
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	210		460	
h _{FE} ratio *1	h _{FE} (Small/Large)	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	0.50	0.99		
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	\mathbf{f}_{T}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

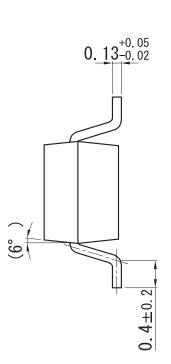
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *1: Ratio between 2 elements

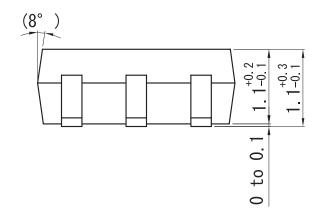




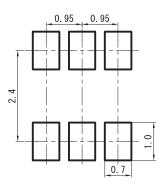
Mini6-G4-B







Land Pattern (Reference) (Unit: mm)



Unit: mm

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